

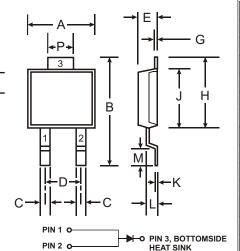
3A HIGH VOLTAGE SCHOTTKY BARRIER RECTIFIER **POWERMITE®3**

Features

- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Reverse Breakdown Voltage
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity **Protection Applications**

Mechanical Data

- Case: POWERMITE®3, Molded Plastic
- Plastic Material: UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram Marking: See Page 3
- Weight: 0.072 grams (approx.)
- Ordering Information: See Page 3



Pins 1 & 2 must be electrically irNote: connected at the printed circuit board.

POWERMITE®3				
Dim	Min	Max		
Α	4.03	4.09		
В	6.40	6.61		
С	.864	.914		
D	1.83 NOM			
E	1.10	1.14		
G	.173	.203		
Н	5.01	5.17		
J	4.37 4.43			
K	.173 .203			
L	.71	.77		
M	.36	.46		
Р	1.73	1.83		
All Dimensions in mm				

Maximum Ratings @ T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

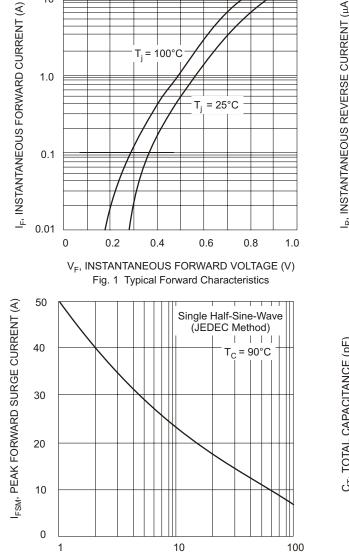
Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	100	V
RMS Reverse Voltage	V _{R(RMS)}	70	V
Average Rectified Output Current (Also see Figure 5)	I _O	3	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave Superimposed on Rated Load (JEDEC Method) @ T _C = 90°C	I _{FSM}	50	А
Typical Thermal Resistance Junction to Soldering Point	R _{θJS}	3.5	°C/W
Typical Thermal Resistance Junction to Case	R ₀ JC	1.6	°C/W
Operating Temperature Range	Tj	-55 to +125	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 1)	V _{(BR)R}	100	_	_	V	I _R = 0.2mA
Forward Voltage (Note 1)	V _F	_ _ _	0.72 0.60 0.80 0.69	0.76 — — —	V	$\begin{array}{l} I_F = 3A, \ T_j = 25^{\circ}C \\ I_F = 3A, \ T_j = 100^{\circ}C \\ I_F = 6A, \ T_j = 25^{\circ}C \\ I_F = 6A, \ T_j = 100^{\circ}C \end{array}$
Reverse Current (Note 1)	I _R		3 0.35	100 20	μA mA	$T_j = 25^{\circ}C$, $V_R = 100V$ $T_j = 100^{\circ}C$, $V_R = 100V$
Total Capacitance	Ст	_	100	_	pF	f = 1.0MHz, V _R = 4.0V DC

Notes: 1. Short duration test pulse used to minimize self-heating effect.





NUMBER OF CYCLES AT 60 Hz Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

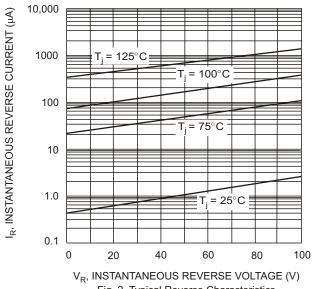
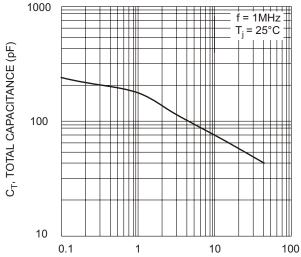
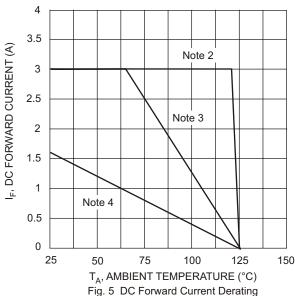


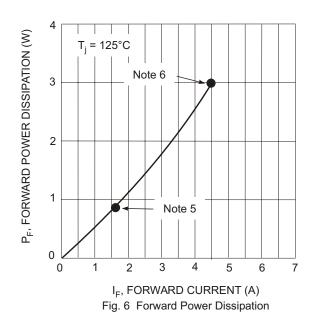
Fig. 2 Typical Reverse Characteristics



V_R, REVERSE VOLTAGE (V) Fig. 4 Typical Total Capacitance vs. Reverse Voltage







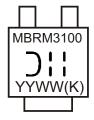
Ordering Information (Note 7)

Device	Packaging	Shipping
MBRM3100-13	POWERMITE®3	5000/Tape & Reel

Notes:

- 2. $T_A = T_{SOLDERING\ POINT}$, $R_{\theta JS} = 3.5^{\circ}C/W$, $R_{\theta SA} = 0^{\circ}C/W$.
- Device mounted on GETEK substrate, 2"x2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". R_{θJA} in range of 30-35°C/W.
- Device mounted on FR-4 substrate, 2"x2", 2 oz. copper, single-sided, pad layout as per Diodes Inc. suggested pad layout document AP02001 which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. R_{θJA} in range of 115-125°C/W.
- 5. Maximum power dissipation when the device is mounted in accordance to the conditions described in Note 4.
- 6. Maximum power dissipation when the device is mounted in accordance to the conditions described in Note 3.
- 7. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



POWERMITE is a registered trademark of Microsemi Corporation.